

OptiMOS[™]3 Power-Transistor


Features

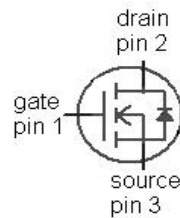
- Ideal for high frequency switching
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21

Product Summary

| | | |
|------------------|-----|------------|
| V_{DS} | 80 | V |
| $R_{DS(on),max}$ | 9.6 | m Ω |
| I_D | 73 | A |



| | |
|----------------|--|
| Type | IPD096N08N3 G |
| |  |
| Package | PG-TO252-3 |
| Marking | 096N08N |



Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|--|-------------------|---|-------------|------|
| Continuous drain current | I_D | $T_C=25\text{ °C}^{2)}$ | 73 | A |
| | | $T_C=100\text{ °C}$ | 52 | |
| | | | | |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | $T_C=25\text{ °C}$ | 292 | |
| Avalanche energy, single pulse ³⁾ | E_{AS} | $I_D=46\text{ A}$, $R_{GS}=25\text{ }\Omega$ | 90 | mJ |
| Gate source voltage | V_{GS} | | ± 20 | V |
| Power dissipation | P_{tot} | $T_C=25\text{ °C}$ | 100 | W |
| Operating and storage temperature | T_j , T_{stg} | | -55 ... 175 | °C |
| IEC climatic category; DIN IEC 68-1 | | | 55/175/56 | |

¹⁾ J-STD20 and JESD22

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|---|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 1.5 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | minimal footprint | - | - | 75 | |
| | | 6 cm ² cooling area ⁴⁾ | - | - | 50 | |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

| | | | | | | |
|----------------------------------|---------------|--|----|------|------|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$ | 80 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=46\text{ }\mu\text{A}$ | 2 | 2.8 | 3.5 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$ | - | 0.1 | 1 | μA |
| | | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | - | 10 | 100 | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$ | - | 1 | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}, I_D=46\text{ A}$ | - | 7.9 | 9.6 | m Ω |
| | | $V_{GS}=6\text{ V}, I_D=23\text{ A}$ | - | 10.5 | 17.8 | |
| Gate resistance | R_G | | - | 1.6 | - | Ω |
| Transconductance | g_{fs} | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=46\text{ A}$ | 30 | 60 | - | S |

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=40\text{ V},$ $f=1\text{ MHz}$ | - | 1810 | 2410 | pF |
| Output capacitance | C_{oss} | | - | 490 | 652 | |
| Reverse transfer capacitance | C_{rss} | | - | 20 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$ $I_D=40\text{ A}, R_{G,ext}=1.6\ \Omega$ | - | 13 | - | ns |
| Rise time | t_r | | - | 30 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 23 | - | |
| Fall time | t_f | | - | 5 | - | |

Gate Charge Characteristics⁵⁾

| | | | | | | |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=40\text{ V}, I_D=46\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 9 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 5 | - | |
| Switching charge | Q_{sw} | | - | 10 | - | |
| Gate charge total | Q_g | | - | 26 | 35 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.2 | - | V |
| Output charge | Q_{oss} | $V_{DD}=40\text{ V}, V_{GS}=0\text{ V}$ | - | 35 | 47 | nC |

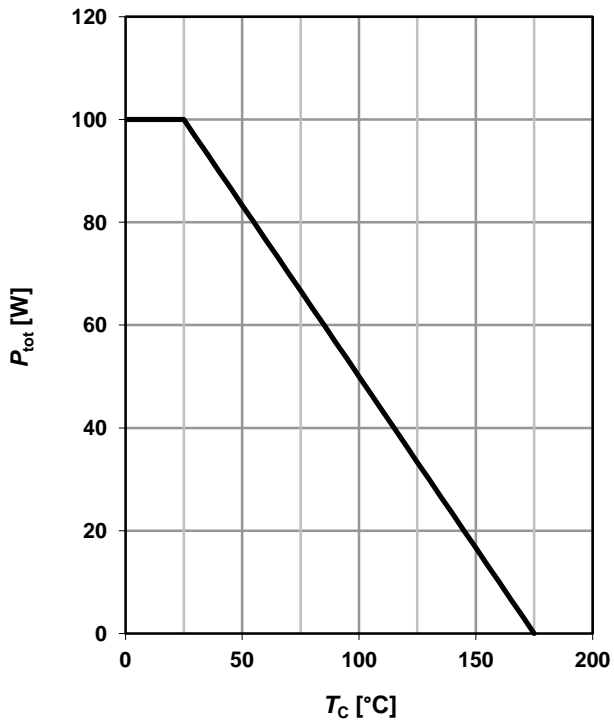
Reverse Diode

| | | | | | | |
|----------------------------------|---------------|---|---|-----|-----|----|
| Diode continuous forward current | I_S | $T_C=25\text{ °C}$ | - | - | 74 | A |
| Diode pulse current | $I_{S,pulse}$ | | - | - | 296 | |
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=46\text{ A},$ $T_j=25\text{ °C}$ | - | 1.0 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=40\text{ V}, I_F=40\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 57 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 91 | - | nC |

⁵⁾ See figure 16 for gate charge parameter definition

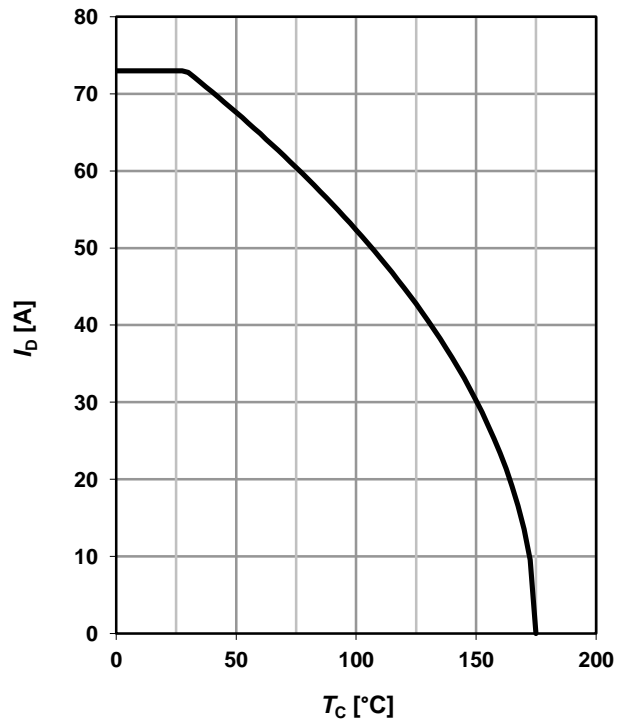
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



2 Drain current

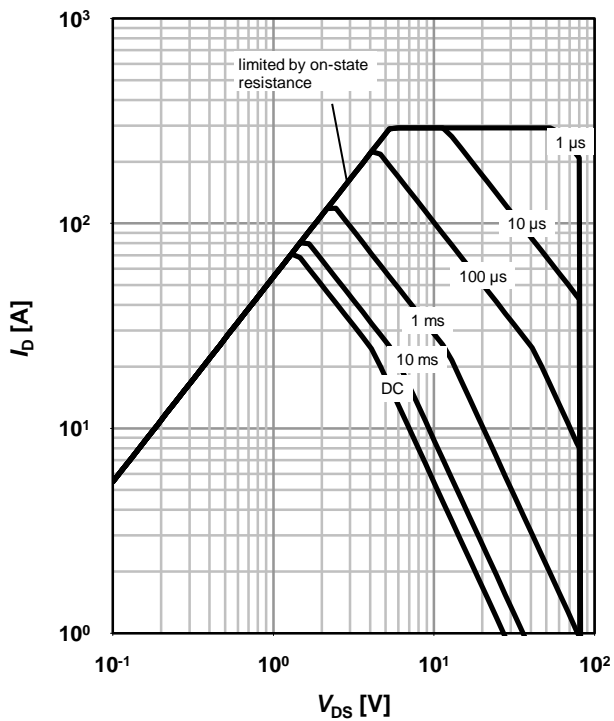
$$I_D = f(T_C); V_{\text{GS}} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ }^{\circ}\text{C}; D = 0$$

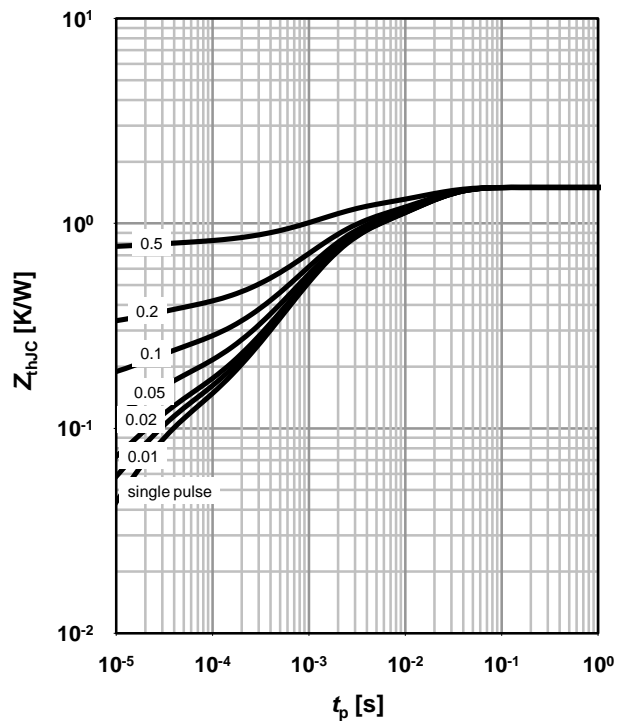
parameter: t_p



4 Max. transient thermal impedance

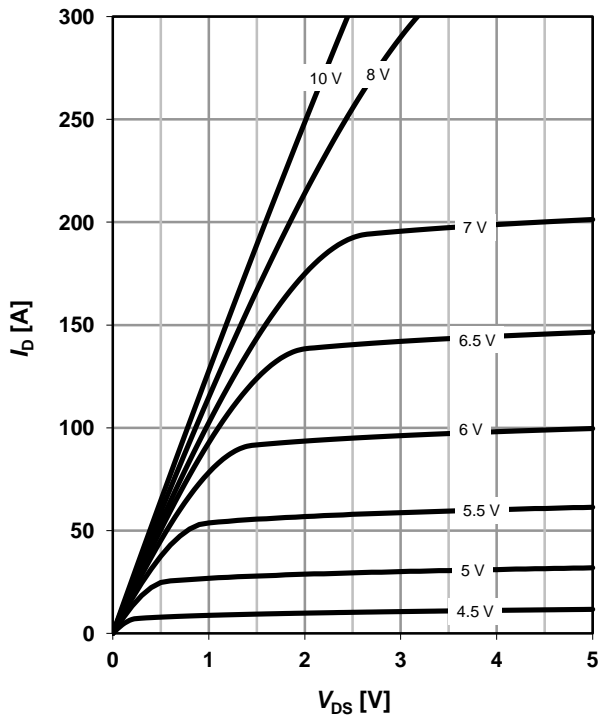
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p/T$



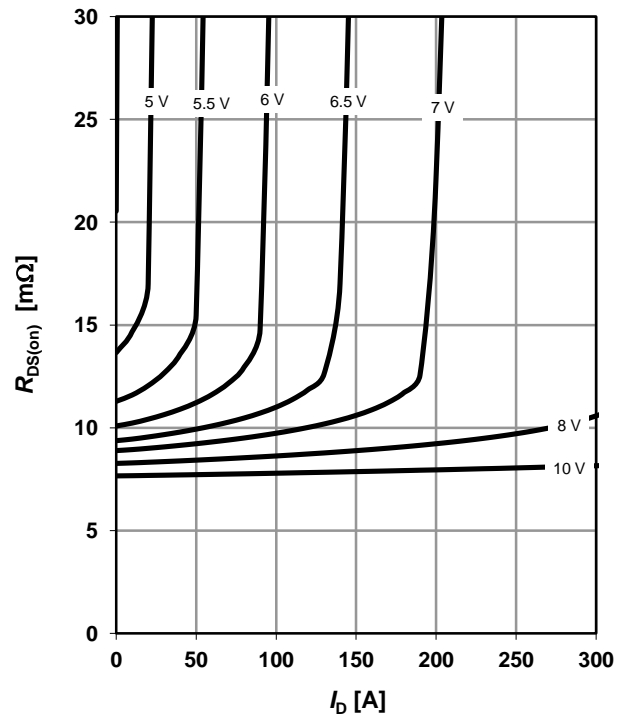
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


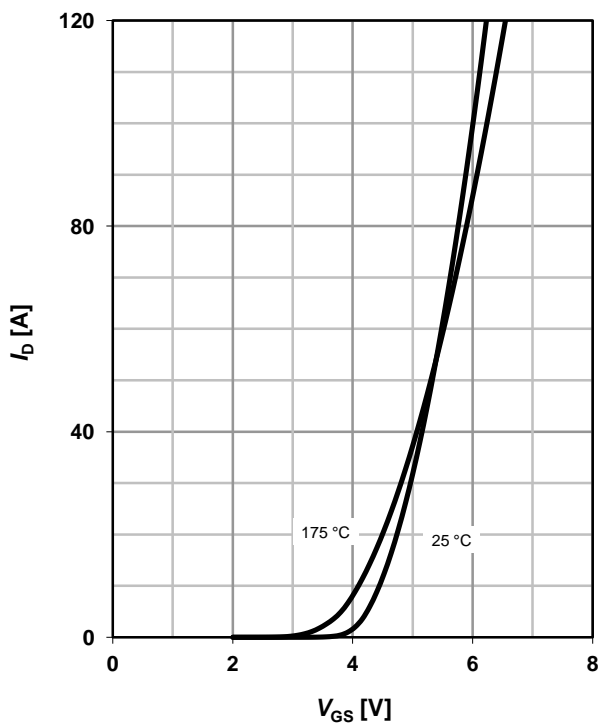
6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

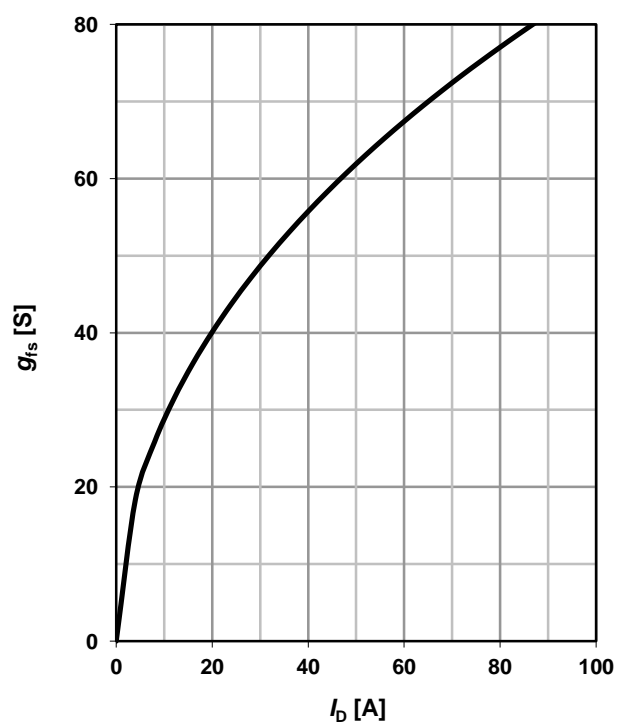
parameter: V_{GS}


7 Typ. transfer characteristics

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

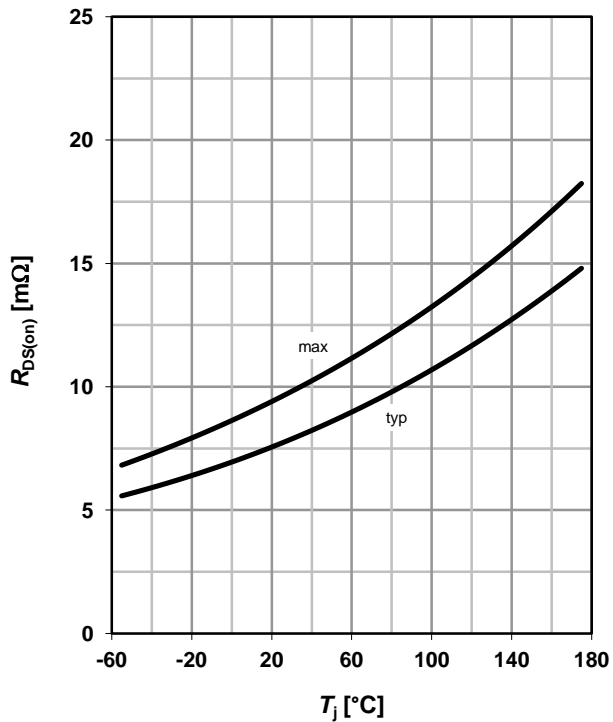
parameter: T_j


8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$


9 Drain-source on-state resistance

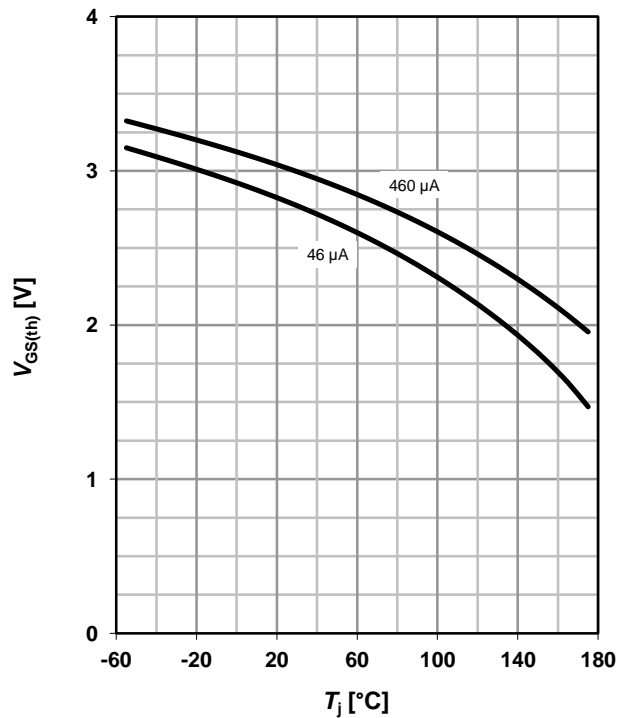
$$R_{DS(on)} = f(T_j); I_D = 46 \text{ A}; V_{GS} = 10 \text{ V}$$



10 Typ. gate threshold voltage

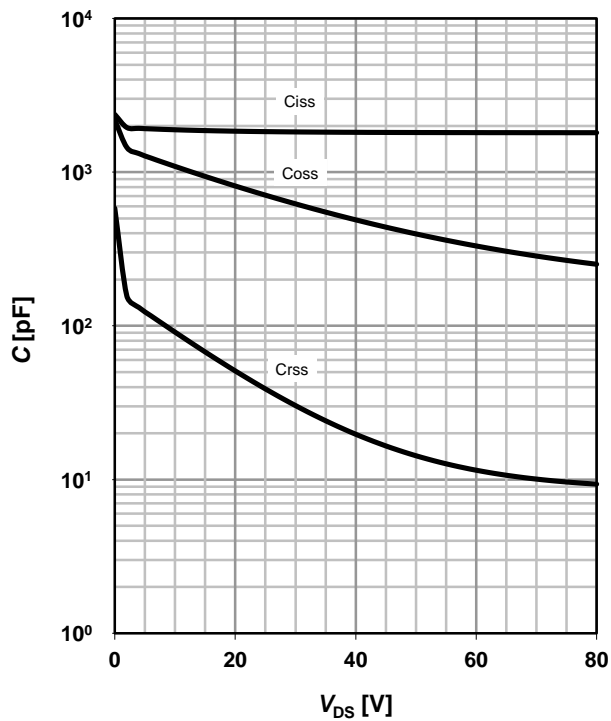
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



11 Typ. capacitances

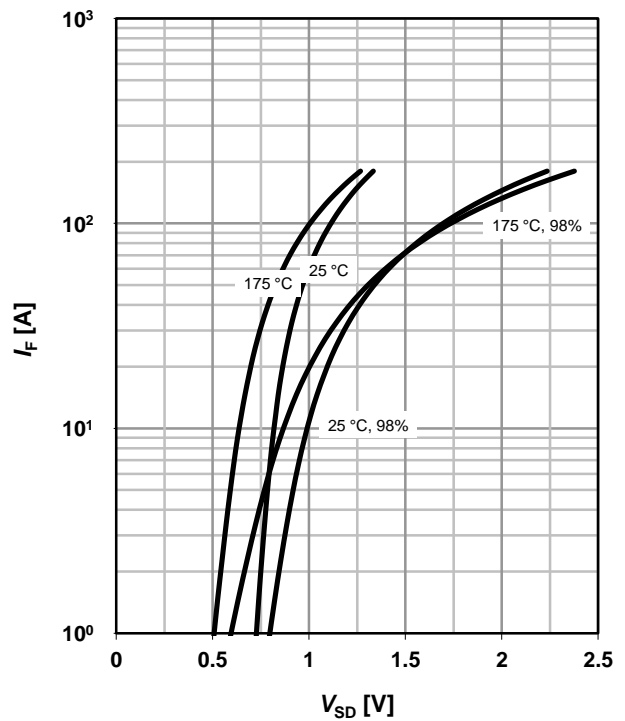
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

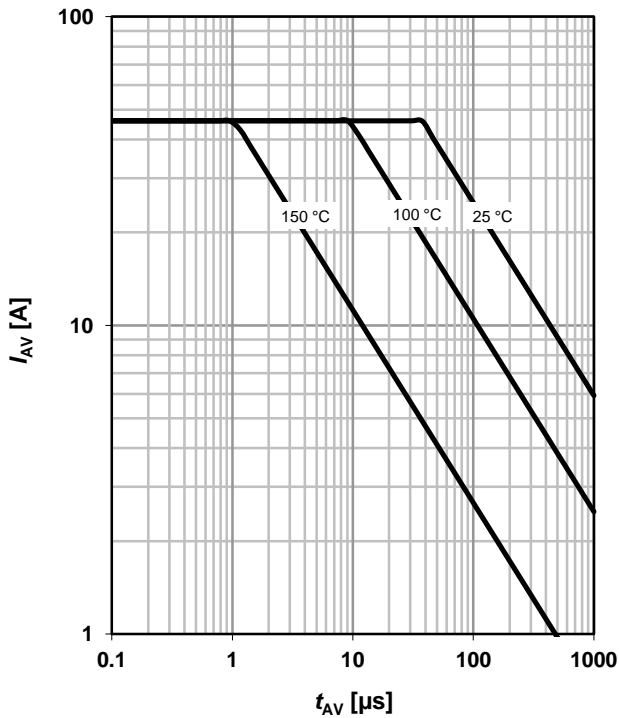
parameter: T_j



13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

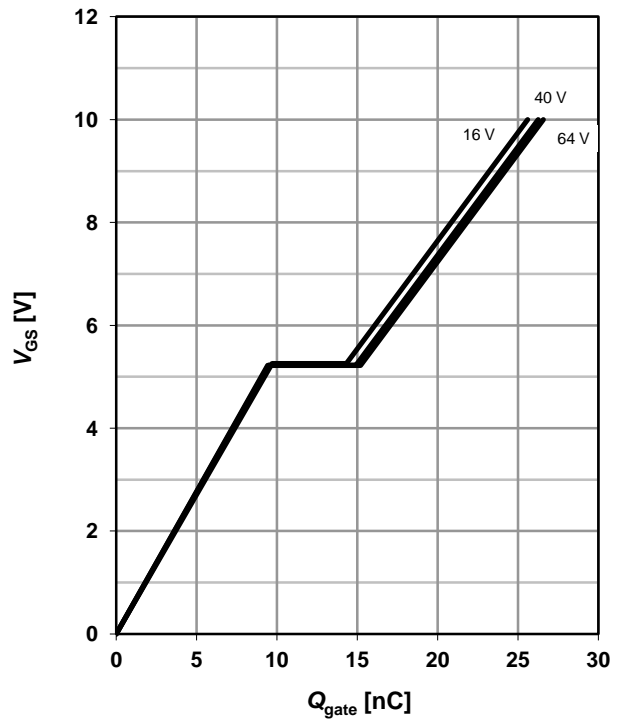
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

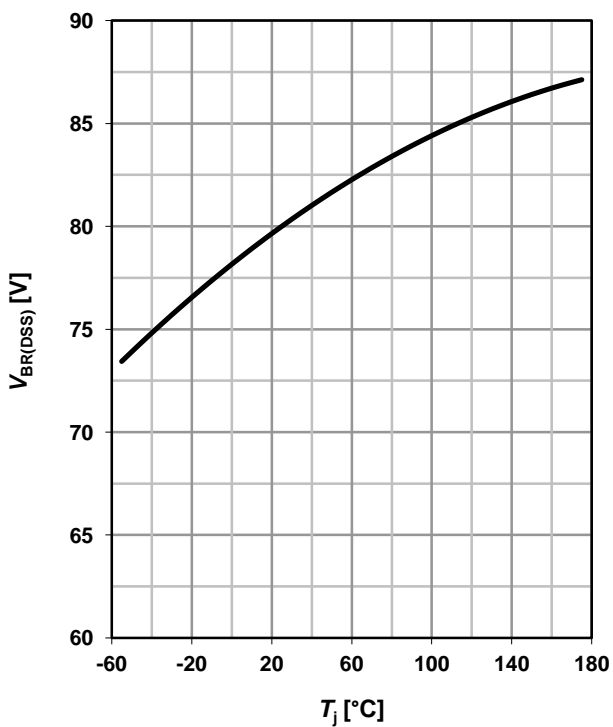
$$V_{GS}=f(Q_{\text{gate}}); I_D=46\ \text{A pulsed}$$

parameter: V_{DD}

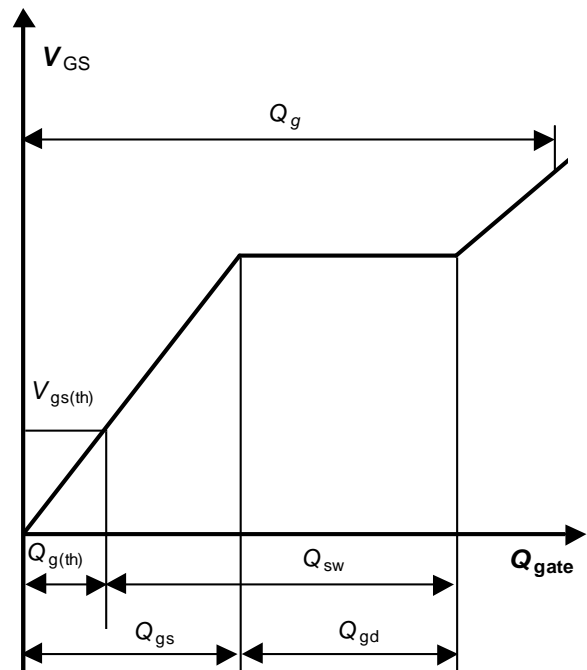


15 Drain-source breakdown voltage

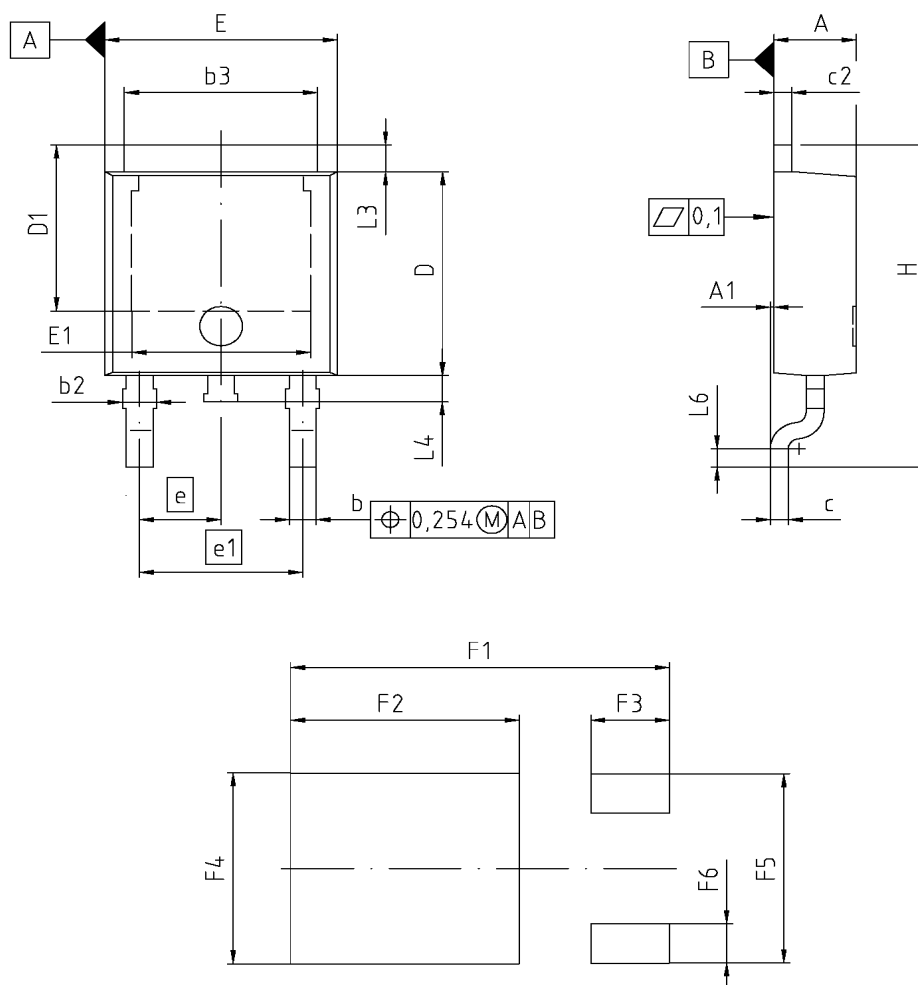
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



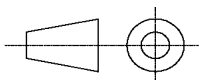
16 Gate charge waveforms



PG-T0252-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|--------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 2.159 | 2.413 | 0.085 | 0.095 |
| A1 | 0.000 | 0.150 | 0.000 | 0.006 |
| b | 0.635 | 0.889 | 0.025 | 0.035 |
| b2 | 0.650 | 1.150 | 0.026 | 0.045 |
| b3 | 5.004 | 5.500 | 0.197 | 0.217 |
| c | 0.457 | 0.580 | 0.018 | 0.023 |
| c2 | 0.460 | 0.980 | 0.018 | 0.039 |
| D | 5.969 | 6.223 | 0.235 | 0.245 |
| D1 | 5.020 | 5.842 | 0.198 | 0.230 |
| E | 6.400 | 6.731 | 0.252 | 0.265 |
| E1 | 4.850 | 5.207 | 0.191 | 0.205 |
| e | 2.286 | | 0.090 | |
| e1 | 4.572 | | 0.180 | |
| N | 3 | | 3 | |
| H | 9.400 | 10.480 | 0.370 | 0.413 |
| L3 | 0.900 | 1.143 | 0.035 | 0.045 |
| L4 | 0.584 | 0.950 | 0.023 | 0.037 |
| L6 | 0.510 | 0.686 | 0.020 | 0.027 |
| F1 | 10.500 | 10.700 | 0.413 | 0.421 |
| F2 | 6.300 | 6.500 | 0.248 | 0.256 |
| F3 | 2.100 | 2.300 | 0.083 | 0.091 |
| F4 | 5.700 | 5.900 | 0.224 | 0.232 |
| F5 | 5.660 | 5.860 | 0.222 | 0.231 |
| F6 | 1.100 | 1.300 | 0.043 | 0.051 |

| |
|---|
| REFERENCE JEDEC TO252 |
| SCALE 0 2.0 4mm |
| EUROPEAN PROJECTION  |
| ISSUE DATE 21-09-2005 |
| FILE TO252_1 |

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